Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	23	nanocrystalline with polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/17 23:30
S2	415	nanocrystalline with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/17 23:31
S3	15	nanocrystalline with silicon and substrate with ("690" or "700")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/17 23:34
S4	96	nanocrystalline with silicon and substrate with heat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/17 23:35
S5	16	nanocrystalline with silicon and substrate with heat\$3 and lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 13:47
S6	6	nanocrystalline with silicon and substrate with heat\$3 same lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 13:47
S7	161	nano\$9 with silicon and substrate with heat\$3 same lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 14:38
S8	0	nanopolysilicon and substrate with heat\$3 same lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 13:49

S9	0	nanopolysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 13:49
S10	20	nanosilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 13:53
S11	0	S10 and substrate with heat\$3 same lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 13:49
S12	0	S10 heat\$3 same lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 13:49
S13	0	S10 heat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 13:49
S14	54	"5754477 "	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 14:08
S15	182	nano-crystal with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 14:37
S16	49	nano-crystal with silicon and heat\$3 same substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 14:09

S17	0	nano-crystal with silicon and heat\$3 same substrate same lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 14:09
S18	49	nano-crystal with silicon and heat\$3 same substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 14:09
S19	6	nano-crystal with silicon same heat\$3 same substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 14:36
S20	0	nano-crystal with silicon same heat\$3 same substrate same lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 14:36
S21	37	nano\$9 near silicon and substrate with heat\$3 same lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 15:26
S22	0	nanograin near silicon and substrate with heat\$3 same lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 15:00
S23	0	nano-grain near silicon and substrate with heat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 15:00
S24	3	nano-grain with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 15:02

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S25	10	nano-grain same silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/18 15:02
S26	125	(438/764).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/18 15:26
S27	2522	substrate with heat\$3 and nano\$9 with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 22:46
S28	18052	substrate with heat\$3 and nano\$9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 22:46
S29	900	substrate with heat\$3 same lamp and nano\$9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 22:46
S31	161	substrate with heat\$3 same lamp and nano\$9 with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 22:46
S32	68	substrate near heat\$3 same lamp and nano\$9 with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 22:47
S33	41	substrate near heat\$3 with lamp and nano\$9 with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 22:48

S34	3	substrate near heat\$3 with lamp and nanocrystal\$4 with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 22:50
S35	6	substrate with heat\$3 with lamp and nanocrystal\$4 with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 22:56
S36	0	substrate with heat\$3 with lamp and nano-crystal\$4 with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 22:57
S37	0	substrate with heat\$3 same lamp and nano-crystal\$4 with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 22:57
S38	9	substrate with heat\$3 same lamp and nanocrystal\$4 with silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:05
S39	29	substrate with heat\$3 with lamp and nanocrystal\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:09
S40	0	"CHAKRAVARTI-ASHIMA.in."	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:09
S41	0	"CHAKRAVARTI-ASHIMA.in."	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:10

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S42	21	CHAKRAVARTI-ASHIMA-B.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:35
S43	0	power with lamp with workpiece same polysilicon deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:36
S44	0	power with lamp with substrate same polysilicon deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:36
S45	1	power with lamp with substrate same polysilicon with deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:37
S46	3	power with lamp with substrate same polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:39
S47	0	lamp with backside with substrate same polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:40
S48	0	lamp with lower surface with substrate same polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:40
S49	121	lamp with substrate same polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:41

S50	993	(438/795).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;	OR	OFF	2006/03/19 23:42
			IBM_TDB			
S51	227	(438/799).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/19 23:42
S52	299	S50 and lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:42
S53	90	S50 and lamp and polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/20 00:29
S54	0	S50 and lamp and polysilicon and nanocrystal\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:45
S55	0	S50 and lamp and nanocrystal\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:45
S56	1	S50 and nanocrystal\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/19 23:45
S57	95	lamp with below with substrate and polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/20 00:55

S58	22	lamp with below with substrate and polysilicon with cvd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/20 00:59
S59	30	lamp with below with substrate and polysilicon same cvd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/20 01:01
S60	1	lamp with below with substrate and nanograin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/20 01:02
S61	77	nanograin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/20 01:07
S62	33	nanograin and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/20 01:08
S63	1962	nanocrystal and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/20 01:08
S64	77	nanocrystal and silicon and cvd and lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/20 01:14
S65	1120	(438/488).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 01:14

S66	71	(438/495).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 01:14
S67	993	(438/795).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 01:14
S68	0	S64 and S67	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/20 01:16
S69	64	S64 and cvd and lamp and power	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/20 01:16
S70	42	lamp with heat\$3 same polysilicon with deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/07 01:39
S71	3	lamp with heat\$3 with power same polysilicon with deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/07 01:39
S72	22	lamp with heat\$3 same backside and polysilicon with deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:39
S73	3	("6903016").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/11 17:16

S74	3	("6610151").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/11 17:47
S75	2	("6136707").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/11 18:13
S76	2	("6518668").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/11 18:13
S77	0	heat with power with substrate same silicon deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:50
S78	0	heat with power same substrate same silicon deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:50
S79	0	lamp with power same substrate same silicon deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:51
S80	14	lamp with power same substrate same silicon with deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:52
S81	0	lamp with power same backside with (wafer or substrate) same silicon with deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:52

S82	0	lamp with power same backside same (wafer or substrate) same silicon with deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:53
S83	7	lamp with power same backside same (wafer or substrate) same deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:57
S84	51	heat with lamp with power same backside same (wafer or substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:58
S85	49	heat with lamp with power same backside same (wafer or substrate) and deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:58
S86	1093453	heat with lamp with power same backside same (wafer or substrate) and deposition with polysilicon or silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:58
S87	42	heat with lamp with power same backside same (wafer or substrate) and deposition with (polysilicon or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:59
S88	28	heat with lamp with power with backside same (wafer or substrate) and deposition with (polysilicon or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:59
S89	33	heat with lamp with power same backside with (wafer or substrate) and deposition with (polysilicon or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:59

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S90	28	heat with lamp with power with backside with (wafer or substrate) and deposition with (polysilicon or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:59
S91	0	heat with lamp with power with backside with (wafer or substrate) same deposition with (polysilicon or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 01:59
S92	28	heat with lamp with power with backside with (wafer or substrate) and deposition with (polysilicon or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 02:07
S93	0	heat with lamp with power with backside with (wafer or substrate) same deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 02:00
S94	28	heat with lamp with power with (backside or rear) with (wafer or substrate) and deposition with (polysilicon or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 02:10
S95	0	heat with lamp with power with (backside or rear) with (wafer or substrate) same deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 02:10
S96	0	lamp with power with (backside or rear) with (wafer or substrate) same deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 02:11
S97	43	radiation with (backside or rear) with (wafer or substrate) same deposition	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 02:11

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S98	5	radiation with (backside or rear) with (wafer or substrate) same deposition with (polysilicon or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 02:13
S99	241	(438/799).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/12 03:04
S10 0	1107	(438/795).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/12 03:04
S10 1	31	S100 and ((lower with surface) or bottom) and radiation with power	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 20:10
S10 2	57	polysilicon and (lower or bottom) with heating with power with lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 21:50
S10 3	2	polysilicon same (lower or bottom) with heating with power with lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 20:14
S10 4	117	silicon and (lower or bottom) with heating with power with lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/12 23:49
\$10 5	75	silicon with deposition and (lower or bottom) with heating with power with lamp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/13 00:36

S10 6	1	("9675220").PN.	US-PGPUB; USPAT;	OR	OFF	2006/10/13 00:36
			USOCR;			
			EPO; JPO; DERWENT;			
			IBM_TDB	ļ		